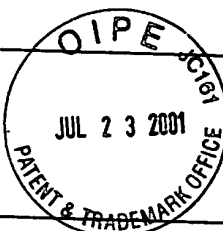


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APPLICANT(S): Tim Anderson

FILING DATE
12/12/2000

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2813

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
LAK	AA 5 6 2 5 2 0 2	4/1997	Chai			
AB						
AC						
AD						
AE						
AF						

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FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
LAL AG 0 8 4 6 7 9 1	10/1998	EPO			
AH					
AI					
AJ					

OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.)

LAK	AK	+	S. Nakamura, M. Senoh, S. Nagahama, N. Iwasa, <i>et al.</i> , "Continuous-wave operation of InGaN/GaN/AlGaIn-based laser diodes grown on GaN substrates" 1998 <i>Appl. Phys. Lett.</i> , 72, 16, 2014.
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EXAMINER

LAK

DATE CONSIDERED

9/1/03

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.